# Power MOSFET 30V, 180mΩ, 1.8A, Single N-Channel

This low-profile high-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

#### **Features**

- Low On-Resistance
- 4V drive
- Low Capacitance
- Pb-Free, Halogen Free and RoHS compliance
- Ultra small package SCH6 (1.6mm×1.6mm×0.56mmt)

# **Typical Applications**

• Load Switch

#### **SPECIFICATIONS**

**ABSOLUTE MAXIMUM RATING** at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	30	<b>V</b>
Gate to Source Voltage	VGSS	±20	٧
Drain Current (DC)	ID	1.8	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	7.2	Α
Power Dissipation When mounted on ceramic substrate (900mm²×0.8mm)	PD	0.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

- Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
  - 2 : This product is designed to "ESD immunity<200V\*", so please take care when handling.
    - \*Machine Model

# THERMAL RESISTANCE RATINGS

THERMAL REGISTANCE RATINGS						
Parameter	Symbol	Value	Unit			
Junction to Ambient When mounted on ceramic substrate (900mm <sup>2</sup> × 0.8mm)	R <sub>θ</sub> JA	156.2	°C/W			

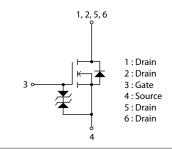


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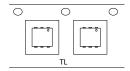
VDSS	R <sub>DS</sub> (on) Max	ID Max
30V	180mΩ@ 10V	4.04
	330mΩ@ 4V	1.8A

# ELECTRICAL CONNECTION N-Channel



#### **PACKING TYPE: TL**

**MARKING** 





#### **ORDERING INFORMATION**

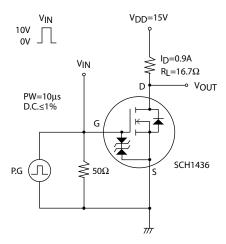
See detailed ordering and shipping information on page 5 of this data sheet.

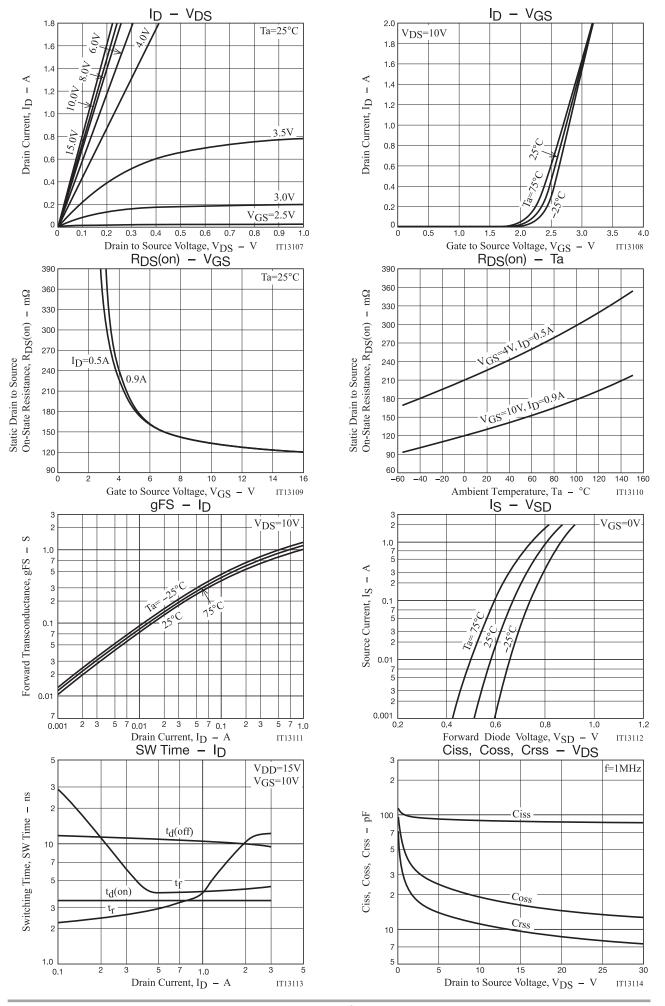
## **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 3)

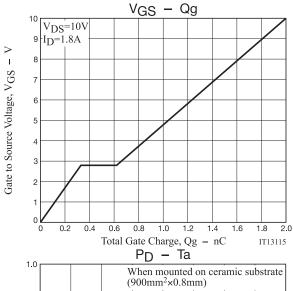
Parameter	Cumphal	Conditions	Value			Unit
Parameter	Symbol	Conditions	min	typ	max	Offic
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transconductance	gFS .	V <sub>DS</sub> =10V, I <sub>D</sub> =0.9A		1.1		S
Static Drain to Source On-State	R <sub>DS</sub> (on)1	I <sub>D</sub> =0.9A, V <sub>GS</sub> =10V		135	180	$m\Omega$
Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.5A, V <sub>GS</sub> =4V		230	330	$m\Omega$
Input Capacitance	Ciss			88		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		19		pF
Reverse Transfer Capacitance	Crss			11		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			3.4		ns
Rise Time	tr	Con an arified Took Circuit		4.0		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		10.4		ns
Fall Time	tf			4.2		ns
Total Gate Charge	Qg			2.0		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =1.8A		0.33		nC
Gate to Drain "Miller" Charge	Qgd			0.29		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.8A, V <sub>GS</sub> =0V		0.86	1.2	V

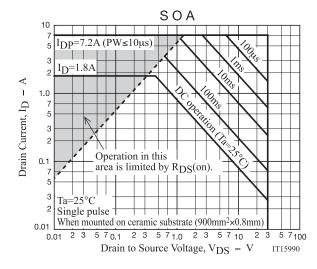
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

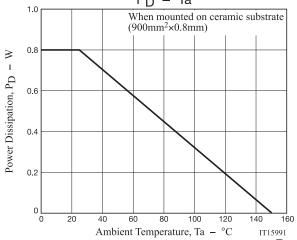
# **Switching Time Test Circuit**

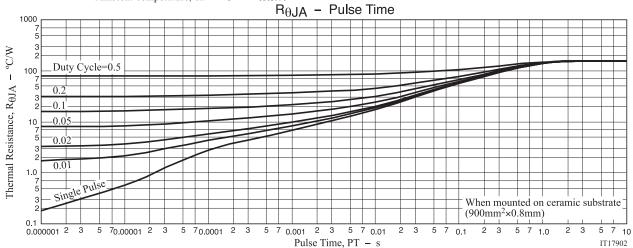






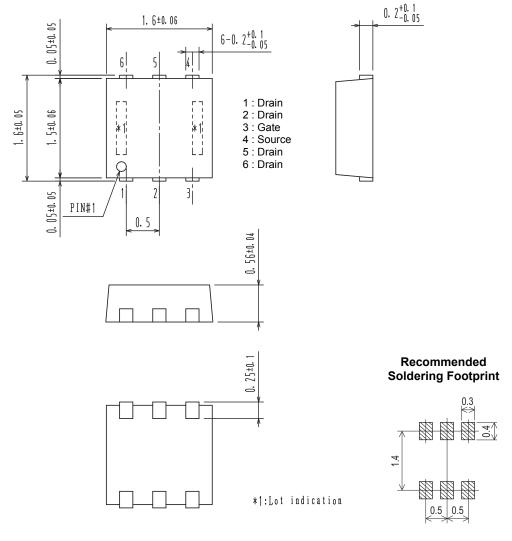






#### PACKAGE DIMENSIONS

unit: mm SOT-563 / SCH6 CASE 463AB ISSUE O



#### ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
SCH1436-TL-H	714	SOT-563 / SCH6	5,000 / Tape & Reel	
SCH1436-TL-W	ZM	(Pb-Free / Halogen Free)		

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the SCH1436 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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